

Nikolay Arutyunov

List of Publications by Year in descending order

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| # | ARTICLE | IF | CITATIONS |
|----|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----------|
| 1 | Microstructure of bismuth centers in silicon before and after irradiation with 15 MeV protons. <i>Journal of Physics Condensed Matter</i> , 2021, 33, 245702. | 1.8 | 0 |
| 2 | Positron probing of open vacancy volume of phosphorus-vacancy complexes in float-zone n-type silicon irradiated by 0.9 MeV electrons and by 15 MeV protons. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2017, 14, 1700120. | 0.8 | 1 |
| 3 | Positron probing of disordered regions in neutron-irradiated silicon. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 2175-2179. | 1.5 | 3 |
| 4 | Positron annihilation lifetime in float-zone n-type silicon irradiated by fast electrons: a thermally stable vacancy defect. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016, 13, 807-811. | 0.8 | 3 |
| 5 | Monovacancy-As complexes in proton-irradiated Ge studied by positron lifetime spectroscopy. <i>Acta Materialia</i> , 2015, 83, 473-478. | 7.9 | 10 |
| 6 | Formation and annealing of vacancy-P complexes in proton-irradiated germanium. <i>Acta Materialia</i> , 2015, 100, 1-10. | 7.9 | 11 |
| 7 | Cascade phonon-assisted trapping of positrons by divacancies in n-FZ-Si(P) single crystals irradiated with 15 MeV protons. <i>AIP Conference Proceedings</i> , 2014, , . | 0.4 | 3 |
| 8 | Point Defects in ^{63}Zn -Irradiated Germanium: High- and Low- Momentum Positron Annihilation Study Before and After n-p-Conversion. <i>Solid State Phenomena</i> , 2009, 156-158, 455-460. | 0.3 | 0 |
| 9 | Configuration of DV Complexes In Ge: Positron Probing of Ion Cores. <i>Solid State Phenomena</i> , 2008, 131-133, 89-94. | 0.3 | 3 |
| 10 | Elementally specific electron-positron annihilation radiation emitted from ion cores of group-V impurity-vacancy complexes in germanium. <i>Physica B: Condensed Matter</i> , 2007, 401-402, 609-612. | 2.7 | 2 |
| 11 | Positron probing of point V-group impurity-vacancy complexes in ^{63}Zn -irradiated germanium. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 788-793. | 4.0 | 7 |
| 12 | Positron-sensitive vacancy-type centres in the nitrides: 1D-ACAR data. <i>Physica B: Condensed Matter</i> , 2003, 340-342, 412-415. | 2.7 | 0 |
| 13 | Investigation of vacancy-type complexes in GaN and AlN using positron annihilation. <i>Semiconductors</i> , 2002, 36, 1106-1110. | 0.5 | 3 |
| 14 | Positron annihilation in AlN and GaN. <i>Physica B: Condensed Matter</i> , 2001, 308-310, 110-113. | 2.7 | 3 |
| 15 | Positron Trapping by Oxygen-Related Defects in Silicon and Anisotropy of 1D-ACAR Spectra. <i>Solid State Phenomena</i> , 1999, 69-70, 333-338. | 0.3 | 4 |
| 16 | Positron Annihilation Rate and Broad Component of 1D-ACAR in Cz-Si and Fz-Si. <i>Solid State Phenomena</i> , 1997, 57-58, 489-494. | 0.3 | 4 |
| 17 | Positron Annihilation on Thermal Defects in Cz-Si and Fz-Si. <i>Solid State Phenomena</i> , 1993, 32-33, 589-594. | 0.3 | 2 |
| 18 | Positron Studies of Thermal-Induced Defects in Silicon. <i>Solid State Phenomena</i> , 1989, 6-7, 435-442. | 0.3 | 2 |

| # | ARTICLE | IF | CITATIONS |
|----|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----------|
| 19 | Similarity of Atomic Configurations of Thermally Stable Positron-Sensitive Complexes Produced with 0.9-MeV Electrons and 15-MeV Protons in α - FZSi:P Crystals. Solid State Phenomena, 0, 242, 296-301. | 0.3 | 2 |